Physics and Technology of High-*k* Gate Dielectrics 6

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Table of Contents

Preface *iii*

Chapter 1
Metal Work Function

Work Function and Effective Oxide Thickness Engineering via Alloying of Metal Gate Electrodes * 3
J. Schaeffer, M. Raymond, D. Gilmer, R. Gregory, B. Taylor, J. Jiang, D. Triyoso, R. Hegde and S. Samavedam

Single Metal/Dual High-k CMISFETs without High-k-induced Vth Variation by MgO or Al2O3 Incorporation * 11
N. Mise, T. Morooka, T. Eimori, T. Ono, Y. Nara and Y. Ohji

Engineering High Dielectric Constant Materials for Band-Edge CMOS Applications 19
H. Jagannathan, V. Narayanan and S. Brown

Fundamental Aspects of Effective Work Function Instability of Metal/Hf-based High-k Gate Stacks * 27
H. Watanabe, S. Yoshida, Y. Kita, T. Hosoi, T. Shimura, K. Shiraishi, Y. Nara and K. Yamada

Chapter 2
Reliability

Universal Correlation Between Mobility and NBTI on Advanced High-k/Metal Gate Stacks * 41
G. Reimbold, X. Garros, M. Casse, M. Rafik, C. Leroux, G. Ribes and F. Martin

Hot Carrier Reliability of ALD HfSiON Gated MOSFETs with Different Compositions 55
H. Chen, S. Chen, C. Lu, C. Liu, F. Chiu, Z. Hsieh, H. Huang, L. Cheng, C. Lin, G. Ma and S. Sun

Inversion Layer Mobility in High-k Dielectric MOSFETs - Intrinsic Mobility Degradation by Electric Dipoles at High-k/SiO2 Interface 67
H. Ota, A. Hirano, Y. Watanabe, N. Yashuda, K. Iwamoto, K. Okada, S. Migita, T. Nabatame and A. Toriumi

Trapping in 1nm EOT high-k / MG * 77
M. Zahid, L. Pantisano, R. Degraeve, M. Aoulaiche, L. Trojman, I. Ferain, E. San Andres, A. Shickova, R. O'Connor, G. Groeseneken, M. Heyns and S. De Gendt

Chapter 3
Interfaces, Traps, and Defects I

Interface Engineering of a Metal/ High-k/ Ge Layered Structure by Water Vapor Discharge * 87
K. Muraoka

Interface Study in a "Metal / High-k" Gate Stack: Tantalum Nitride on Hafnium Oxide 99
C. Gaumer, E. Martinez, S. Lhostis, C. Wiemer, M. Perego, V. Loup, D. Lafond and J. Fabbri

Extraction of Trap Parameters for High-K Gate Stacks 111
S. Kar and S. Rawat

Dielectric and Interface Properties of TiO2/HfSiO/SiO2 Layered Structures Fabricated by in situ PVD Method 121
H. Arimura, Y. Naitou, N. Kitano, Y. Oku, N. Yamaguchi, M. Kosuda, T. Hosoi, T. Shimura and H. Watanabe

Interfacial and Electrical Characterization of HfO2-Gated MOSCs and MOSFETs by C-V and Gated-Diode Method 131
S. Chen, H. Chen, C. Chen, F. Chiu, C. Liu, Z. Hsieh, H. Huang and H. Hwang

Fabrication of High-k/Si Structure Using Metal Deposition Followed by Oxidation 139
Y. Oniki, Y. Iwazaki, M. Hasumi, T. Ueno and K. Kuroiwa

Chapter 4
High-k Gate Stack Characteristics

The Application of X-ray Metrology for Rapid Development of High-k Dielectrics 149
P. Hung, T. Böscke, M. Wormington, D. K. Bowen, P. Lysaght, P. Kirsch, H. Tseng and R. Jammy

Electrical Properties of CeOX /La2O3 Stack as a Gate Dielectric for Advanced MOSFET Technology 153
M. Kouda, K. Tachi, K. Kakushima, P. Ahmet, K. Tsutsui, N. Sugii, A. Chandorkar, T. Hattori and H. Iwai

Electrical and Chemical Properties of the HfO2/SiO2/Si Stack: Impact of HfO2 Thickness and Thermal Budget 161
E. Martinez, C. Leroux, N. Benedetto, C. Gaumer, M. Charbonnier, C. Licitra, C. Guedj, F. Fillot and S. Lhostis

Annealing-temperature Dependence of Compositional Depth Profile and Chemical Structures of LaOx/ScOx/Si and ScOx/LaOx/Si Interfacial Transition Layer 171
H. Nohira, Y. Takenaga, K. Kakushima, P. Ahmet, K. Tsutsui and H. Iwai

Scanning Transmission Electron Microscopy Studies of Interface Stability and Point Defects in Gate Stacks with High-k Dielectrics * 177
S. Stemmer, M. P. Agustin and D. O. Klenov

Chapter 5
Gate Stack Processing I

Study of Kinetic Behaviors of GeO in GeO2/Ge Stacks * 187
K. Kita, C. Lee, T. Nishimura, K. Nagashio and A. Toriumi

Atomic Layer Deposition of High-κ/Metal Gate Stack MOSFET-Devices on Strained Silicon-on-Insulator Substrates 195
C. Henkel, S. Abermann, O. Bethge, M. Reiche and E. Bertagnolli

Electrical Characteristics of Metal/High-k MOS Devices Using Effective Oxygen Control for Sub-1nm EOT 203
K. Okamoto, K. Kakushima, P. Ahmet, K. Tsutsui, N. Sugii, A. Chandorkar, T. Hattori and H. Iwai

Growth and Characterization of Alternative Gate Dielectrics by Molecular-Beam Epitaxy * 213
L. F. Edge, W. Tian, V. Vaithyanathan, T. Heeg, D. Schlom, D. Klenov, S. Stemmer, J. Wang and M. J. Kim

Evaluation of MOCVD Grown Niobium Nitride Films as Gate Electrode for Advanced CMOS Technology 229
T. Thiede, H. Parala, K. Reuter, G. Passing, S. Kirchmeyer, J. Hinz, M. Lemberger, A. Bauer and R. Fischer

MOCVD of Niobium Nitrides and Oxy-Nitrides using an All-Nitrogen-Coordinated Precursor: Thin-film Deposition and Mechanistic Study 235
D. Bekermann, D. Barreca, A. Devi, A. Gasparotto and R. Fischer

Novel Highly Volatile MOCVD Precursors for Ta2O5 and Nb2O5 Thin Films 243
T. Yotsuya, H. Chiba, T. Furukawa, T. Yamamoto, K. Inaba, K. Tada, T. Suzuki, K. Fujimoto, H. Funakubo, T. Yamakawa and N. Oshima

Chapter 6
Alternate Substrates I

In-Situ Studies of Interfacial Bonding of High-k Dielectrics for CMOS Beyond 22nm * 255
R. M. Wallace

Atomic Layer Deposited Lanthanum-(Zirconate/Aluminate) Based High-K Dielectric Stacks For Future CMOS-Technology 273
S. Abermann, C. Henkel, O. Bethge and E. Bertagnolli

Effect of Ultrathin Si Passivation Layer for Ge MOS Structure with La_2O_3 Gate Dielectric 285
J. Song, K. Kakushima, P. Ahmet, K. Tsutsui, N. Sugii, T. Hattori and H. Iwai

Gate Dielectrics for High Mobility Semiconductors * 295
A. Dimoulas, Y. Panayiotatos, P. Tsipas, S. Galata, G. Mavrou, A. Sotiropoulos, C. Marchiori, C. Rossel, D. Webb, C. Andersson, M. Sousa, M. Richter and J. Fompeyrine

Chapter 7
Memory

Mechanism of Charge Storage in nc-RuO Embedded ZrHfO High-k Films 309
C. Lin and Y. Kuo

Thermally Stable Hf-silicate with Modification of Si Doping and Thermal Budget in MIM Capacitors 317
P. Tzeng, T. Wu, C. Wang, C. Lin, L. Lee and M. Tsai

Improved Lower Electrode Oxidation of High-k TiCeO Metal-Insulator-Metal Capacitors by Using Dual Plasma Treatment 323
C. Cheng, H. Hsu, C. Deng, A. Chin and C. Chou

Dielectric Properties of SrTiO3 Thin Films on SrRuO3 Seed Prepared by Plasma-enhanced Atomic Layer Deposition 335
J. Ahn, J. Kim, J. Kim, J. Roh and S. Kang

High Performance Ir/TiPrO/TaN MIM Capacitors for Analog ICs Application 341
C. C. Huang, C. Cheng, A. Chin and C. Chou

Chapter 8
Integration

Organic Mask Removal Assessment for 32nm Fully Depleted SOI Technology with TiN-metal Gate on HfO2 355
L. Lachal, J. Chiaroni, E. Lajoinie, O. Louveau, F. Ritton, P. Lavios, J. Finet, P. Biranceau, A. Arnoux, E. Sauvagnargues, O. Bailloux, G. Medico, C. Tallaron, F. Humbert, N. Rochat and E. Martinez

Chapter 9
Alternate Substrates II

Al2O3/ZrO2/Al2O3 High-k Dielectric Stacks on Germanium Substrates Grown by Atomic Layer Deposition at High and Low Temperatures 365
O. Bethge, S. Abermann, C. Henkel and E. Bertagnolli

Comparison between Direct-Contact HfO_2/Ge and HfO_2/GeO_2/Ge Stack Structures: Physical and Electrical Properties 375
Y. Abe, N. Miyata and T. Yasuda

Plasma Nitridation of HfO2 Gate Dielectric on p-GaAs Substrates 387
G. K. Dalapati, A. Sridhara, A. S. Wong, C. Chia and D. Chi

Chapter 10
Interfaces, Traps, and Defects II

Identifying Performance-Critical Defects in the High-k/Metal Gate Stacks * 395
G. Bersuker, D. Hen, J. Price, A. Neugroschel, H. Tseng and R. Jammy

Interface Properties Improvement of Ge/Al2O3 and Ge/GeO2/Al2O3 Gate Stacks using Molecular Beam Deposition 411
F. Bellenger, C. Merckling, J. Penaud, M. Houssa, M. Caymax, M. Meuris, K. De Meyer and M. Heyns

Interface Characterization of CeO2-Gated MOSFETs Using Gated Diode Method and Charge Pumping Technique 423
F. Chiu, H. W. Chen, C. Chen, C. Liu, S. Chen, B. Huang, Z. Hsieh, H. Huang and H. Hwang

Physical Characterization of the Metal/High-k Layer Interaction upon Annealing 433
T. Conard, A. Franquet, W. Vandervorst, M. Reading, J. Van den Berg, S. Van Elschocht, T. Schram, C. Adelmann and S. De Gendt

Modelling of Layers and Traps in High-K Gate Stacks and Energy Band and Equivalent Circuit Representations 443
S. Kar and S. Rawat

Electrical Characterization of Metal Gate/High-k Dielectrics on GaAs Substrate 455
V. Budhraja and D. Misra

Real Space Surface Reconstructions of Decapped As-rich In0.53Ga0.47As(001)-(2×4) 463
J. Shen, D. L. Winn, W. Melitz, J. B. Clemens and A. C. Kummel

Chapter 11
Gate Stack Processing II

Effects of Low Temperature O2 Treatment on the Electrical Characteristics of Amorphous LaAlO3 Films by Atomic Layer Deposition * 471
Y. Liu, H. Kim, J. Wang, H. Li and R. G. Gordon

Impact of High Pressure O2 Annealing on Amorphous LaLuO3/Ge MIS Capacitors 479
T. Tabata, C. Lee, K. Kita and A. Toriumi

Tuning of Material and Electrical Properties of Strontium Titanates using Process Chemistry and Composition 487
R. Katamreddy, V. Omarjee, B. Feist, C. Dussarrat, M. Singh and C. Takoudis

Effect of Rare-Earth Doping and Nitrogen Passivation Treatments on the Properties of Ultra-thin Hafnia Films 497
S. Ramanathan, A. Karthikeyan, S. Govindarajan and P. Kirsch

Chapter 12
Electrical Characteristics

Capacitance-Voltage (CV) Characterization of GaAs-Oxide Interfaces * 507
G. Brammertz, H. Lin, K. Martens, D. Mercier, C. Merckling, J. Penaud, C. Adelmann, S. Sioncke, W. Wang, M. Caymax, M. Meuris and M. Heyns

Effect of Annealing on Electronic Characteristics of HfSiON Films fabricated by Damascene Gate Process * 521
K. Yamabe, K. Murata, T. Hayashi, T. C. Tamura, M. Sato, A. Uedono, K. Shiraishi, N. Umezawa, T. Chikyow, H. Watanabe, Y. Nara, Y. Ohji, S. Miyazaki, K. Yamada and R. Hasunuma

Author Index 527

** invited paper*